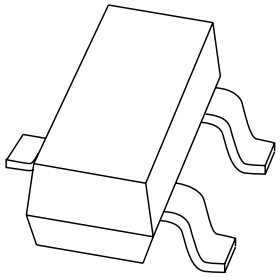
DATA SHEET



PMBS3906
PNP general purpose transistor

Product specification
Supersedes data of 1999 Apr 22

2004 Feb 02

Philips
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PNP general purpose transistor PMBS3906

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complement: PMBS3904.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMBS3906	*O6

Note

1. * = p : Made in Hong Kong.
   * = t : Made in Malaysia.
   * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

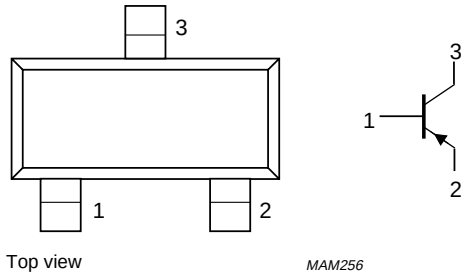


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBS3906	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current capability		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –30 V	–	–50	nA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –5 V	–	–50	nA
h_{FE}	DC current gain	V_{CE} = –1 V; (see Fig.2)			
		I_C = –0.1 mA	60	–	
		I_C = –1 mA	80	–	
		I_C = –10 mA	100	300	
		I_C = –50 mA; note 1	60	–	
		I_C = –100 mA; note 1	30	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA	–	–250	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–	–400	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA	–	–850	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–	–950	mV
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = –5 V; f = 100 MHz	–	4.5	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; VE_B = –0.5 V; f = 100 MHz	–	12	pF
f_T	transition frequency	I_C = –10 mA; V_{CE} = –20 V; f = 100 MHz	150	–	MHz
F	noise figure	I_C = –100 μA; V_{CE} = –5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.3)					
t_{on}	turn-on time	I_{Con} = –10 mA; I_{Bon} = –1 mA; I_{Boff} = 1 mA	–	100	ns
t_d	delay time		–	50	ns
t_r	rise time		–	50	ns
t_{off}	turn-off time		–	700	ns
t_s	storage time		–	600	ns
t_f	fall time		–	100	ns

Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

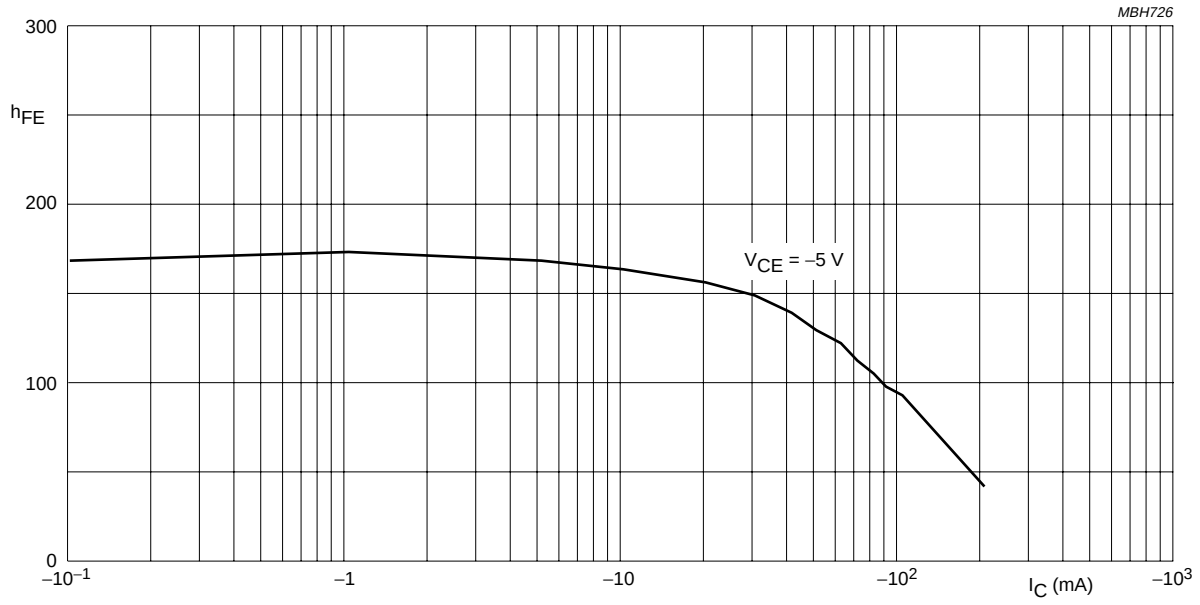
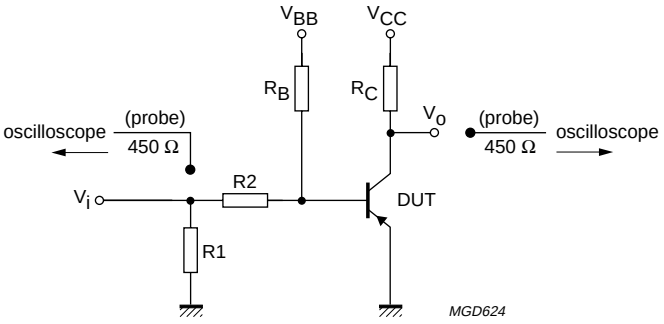


Fig.2 DC current gain; typical values.

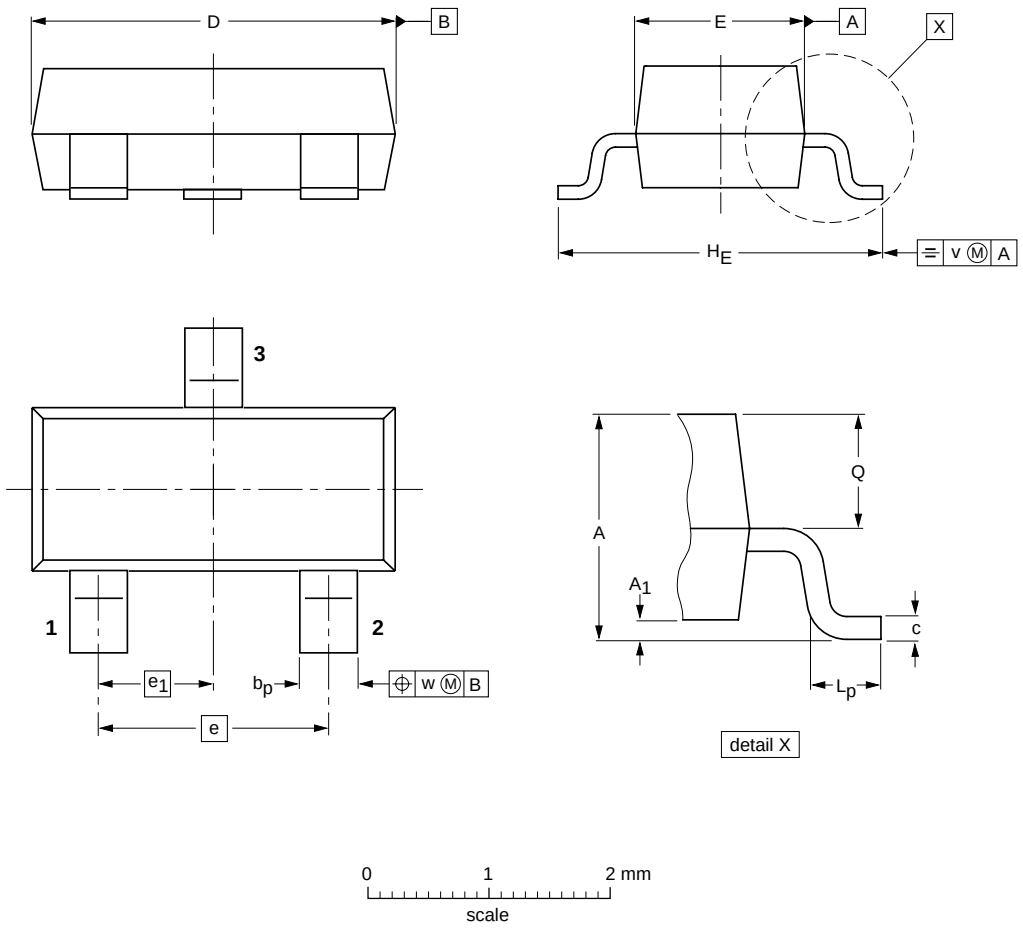


V_i = –5 V; T = 500 µs; t_p = 10 µs; $t_r = t_f \leq 3$ ns.
R1 = 56 Ω; R2 = 2.5 kΩ; R_B = 3.9 kΩ; R_C = 270 Ω.
V_{BB} = 1.9 V; V_{CC} = 3 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.3 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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For additional information please visit **http://www.semiconductors.philips.com**. Fax: **+31 40 27 24825**
For sales offices addresses send e-mail to: **sales.addresses@www.semiconductors.philips.com**.

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